

I. REMARKS

Claims 1-19 are pending in the Application, and of these, claims 13-18 stand withdrawn from consideration upon election of claims 1-12 and 19 pursuant to the Restriction Requirement mailed October 1, 2001. Accordingly, claims 1-12 and 19 are currently under examination. Applicants reserve the right to prosecute non-elected claims 13-18 in one or more continuing or divisional applications. No claim amendments are requested in this Reply.

II. THE REJECTIONS UNDER 35 U.S.C. § 102 AND § 103

Claims 1-4, 6-12, and 19 stand rejected under 35 U.S.C. § 102(e) on the grounds that they are anticipated by U.S. Patent Publication No. 2002/0136910 A1 to Hacker ("Hacker"), which the Examiner alleges claims the priority date of U.S. 6,472,076, filed October 18, 1999. Claim 5 stands rejected over Hacker in view of U.S. Patent No. 5,016,982 to Ferguson et al. ("Ferguson"). Nothing in this Reply should be construed as an admission that Hacker is prior art to the Application.

Applicants respectfully request withdrawal of all rejections over Hacker because Hacker does not teach or suggest an FET device (or any other semiconductor or transistor device) comprising a silsesquioxane film. Applicant's further request withdrawal of all rejections over Hacker in view of Ferguson because Ferguson does not remedy the deficient teachings of Hacker.

Applicants' claims are directed to field effect transistors (FET devices) comprising a silsesquioxane film as a dielectric layer. Applicants teach preparation of the claimed silsesquioxane films by low-temperature cure of silsesquioxane precursors (i.e., less than about 200 °C, preferably, less than 150 °C). See e.g., Specification, page 8, lines 17-18. Reflecting these teachings, Applicants' claim 1 recites:

"wherein the active dielectric layer comprises a low-temperature cured film of at least one liquid deposited silsesquioxane precursor to provide a high-dielectric strength film". Specification, claim 1.

Importantly, in the Specification, applicants teach that the claimed "low temperature cured film" (derived from silsesquioxane precursors) is, in fact, a silsesquioxane. Specification Page 6, lines 20-21.

Hacker does not teach or suggest FET devices comprising silsesquioxane films. Rather, Hacker teaches alkylated siloxane films (derived from silsesquioxanes) as the dielectric layer in

semiconductor devices. Hacker ¶ [0024]. Semiconductor devices comprising Hacker's alkylated siloxane films are completely different from Applicants' claimed devices comprising silsesquioxane films. The confusion between Applicants' claimed invention and the disclosure of Hacker arises because both Hacker and Applicant refer to "silsesquioxanes" frequently in their respective specifications. The devices Hacker discloses, however, comprise alkylated siloxane films (derived from curing silsesquioxanes), Hacker ¶ [0024] and [0101] et seq., while in complete contrast Applicants claim the silsesquioxane films themselves (derived from curing silsesquioxane precursors) for use in devices. The final semiconductor devices employing Hackers "alkylated siloxane films" are completely different from the devices (FET or otherwise) claimed by Applicants that employ the silsesquioxanes themselves.

Ferguson does not remedy the deficient teachings of Hacker. Ferguson contains no teaching or suggestion of FET devices comprising silsesquioxanes as the dielectric layer.

In view of the above, it is clear that neither Hacker nor the combination of Hacker and Ferguson teach or suggest Applicants' claims. Accordingly, withdrawal of the 35 U.S.C. § 102 and § 103 rejections over Hacker and the combination of Hacker with Ferguson is respectfully requested.

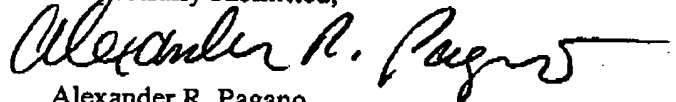
III. CONCLUSION

In view of the above remarks, Applicants have overcome all rejections, and request reconsideration and allowance of the claims. Should the Examiner disagree, Applicants request he notify Applicants' Agent of Record to permit timely scheduling of an Examiner interview. No fee is believed due for entry of this Reply, should any fee be due, however, please charge such fees to Deposit Account number 501358.

IV. AUTHORIZATION FOR TIME EXTENSION UNDER 37 C.F.R. § 1.136(a)

This Reply is believed timely filed within the statutory period of time ending on December 2, 2003 (3 months from the Office Action mailing date of September 2, 2003), therefore, no extensions of time are believed necessary. However, should any extension of time under 37 C.F.R. § 1.136(a) be necessary for entry of this Reply, please consider this paragraph a Petition requesting such extension and the signature below as express authorization for payment of any fees, which should be charged to Deposit Account No. 501358.

Respectfully submitted,



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